Technical Data
TRANSISTOR

DISCRETE SEMICONDUCTOR INDUSTRIES

maximum ratings

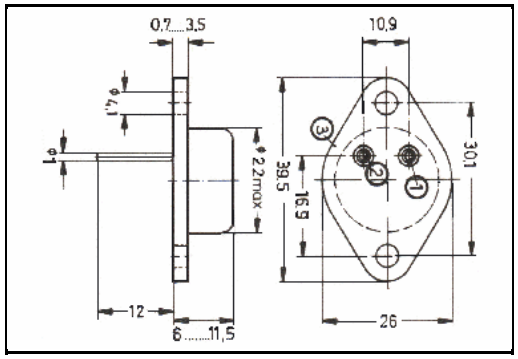
Voltage, Collector to Base (VCBO)	400.0	V	NO.	184T2C
Voltage, Collector to Emitter (VCE)	200.0	V	TYPE	NPN
Voltage, Emitter to Base (VEBO)	10.0	V		
Collector Current (IC)	6.0	A		
Base Current (IB)	3.0	A	CASE	TO-3
Max. Power Dissipation (PT) at TC = 25 °C	87.5	W		
Max. Thermal Resistance (Rth J-C)	2.0	°C/W		
Max. Junction Temperature (TJ)	200.0	°C		

PERFORMANCE CHARACTERISTICS at T_C = 25°C, unless otherwise noted

NO.	SYMBOL	CONDITIONS	MIN.	MAX.	UNITS
1.	BVCEO	IC = 50.0 mA (1)	200.0	-	V
2.	BVCBO	IE = 3.0 mA (1)	400.0	-	V
3.	ICEO	VCE = 200.0 V	-	1.0	mA
4.	ICES	VCE = 300.0 V	-	1.0	mA
5.	IEBO	VEB = 10.0 V	-	1.0	mA
6.	hFE	IC = 2.0 A, VCE = 4.0 V (1)	75.0	180.0	-
7.	VCE(SAT)	IC = 2.0 A, IB = 250.0 mA (1)	-	0.6	V
8.	VBE(SAT)	IC = 2.0 A, IB = 250.0 mA (1)	-	1.2	V
9.	fT	VCE = 15.0 V, IC = 0.5 A, f = 10.0 MHz	10.0	-	MHz
10.	t(ON)	IC = 5.0 A, IB = 1.0 A	-	1.0	µs
11.	tOFF	IC = 5.0 A, IB = 1.0 A	-	6.0	µs
12.					
13.					
14.					
15.					
16.					
17.					
18.					
19.					
20.					

Notes (1)pulse-tested tp ≤ 300 µs, duty cycle ≤ 2 %

DIMENSIONS in mm



Marking 184T2C

Customer GENERAL PURPOSE